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Application Number	10596726
Filing Date	2006-06-22
First Named Inventor	Dan YANSON
Art Unit	2813
Examiner Name	Vicki B. BOOKER
Attorney Docket Number	35832.000130

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YI, H T ET AL, "Effect of dielectric and semiconductor cap layer combinations in impurity free vacancy disordering of an InGaAs/InGaAsP single quantum well structure", *Sae Muli*, Vol. 41, pp.193-8 (Sept. 2000)



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